

L Number	Hits	Search Text	DB	Time stamp
1	126572	(semiconductor\$1 chip\$1 die dice\$1 ic\$2 integrated adj circuit\$1) and (heat thermal\$2) near3 (sink\$3 absorb\$3 dissipat\$3 exchang\$3 remov\$3 transfer\$4)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:45
2	7795	((semiconductor\$1 chip\$1 die dice\$1 ic\$2 integrated adj circuit\$1) and (heat thermal\$2) near3 (sink\$3 absorb\$3 dissipat\$3 exchang\$3 remov\$3 transfer\$4)) and (heat thermal\$2) near3 (sink\$3 absorb\$3 dissipat\$3 exchang\$3 remov\$3 transfer\$4) same (carbon\$6 graphit\$2 diamon)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:47
3	1039	((semiconductor\$1 chip\$1 die dice\$1 ic\$2 integrated adj circuit\$1) and (heat thermal\$2) near3 (sink\$3 absorb\$3 dissipat\$3 exchang\$3 remov\$3 transfer\$4)) and solder\$3 same (carbon\$6 graphit\$2 diamond)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:48
4	34	((semiconductor\$1 chip\$1 die dice\$1 ic\$2 integrated adj circuit\$1) and (heat thermal\$2) near3 (sink\$3 absorb\$3 dissipat\$3 exchang\$3 remov\$3 transfer\$4)) and solder\$3 same (carbon\$6 graphit\$2 diamond)) and solder\$3 same (carbon\$6 graphit\$2 diamond) same (foam por\$3 porosit\$3)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:48
5	34	((semiconductor\$1 chip\$1 die dice\$1 ic\$2 integrated adj circuit\$1) and (heat thermal\$2) near3 (sink\$3 absorb\$3 dissipat\$3 exchang\$3 remov\$3 transfer\$4)) and solder\$3 same (carbon\$6 graphit\$2 diamond)) and solder\$3 same (carbon\$6 graphit\$2 diamond) same (foam por\$3 porosit\$3)) and solder\$3 same (carbon\$6 graphit\$2 diamond)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 17:53
6	0	("wo27776").PN.	USPAT; US-PGPUB; EPO; JPO	2004/02/08 17:53